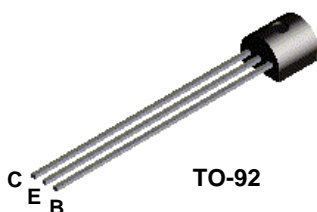
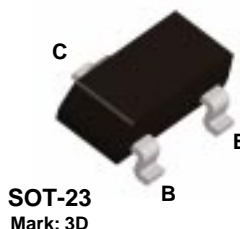


MPSH81



MMBTH81



PNP RF Transistor

This device is designed for general RF amplifier and mixer applications to 250 MHz with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 75.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	20	V
V _{CB0}	Collector-Base Voltage	20	V
V _{EBO}	Emitter-Base Voltage	3.0	V
I _C	Collector Current - Continuous	50	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		MPSH81	*MMBTH81	
P _D	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	125		°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	357	556	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

PNP RF Transistor

(continued)

MPSH81 / MMBTH81

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	20		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_E = 0$	20		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	3.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 10 \text{ V}, I_E = 0$		100	nA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 2.0 \text{ V}, I_C = 0$		100	nA

ON CHARACTERISTICS

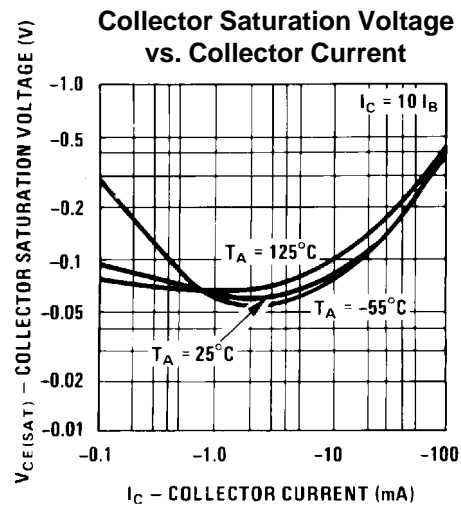
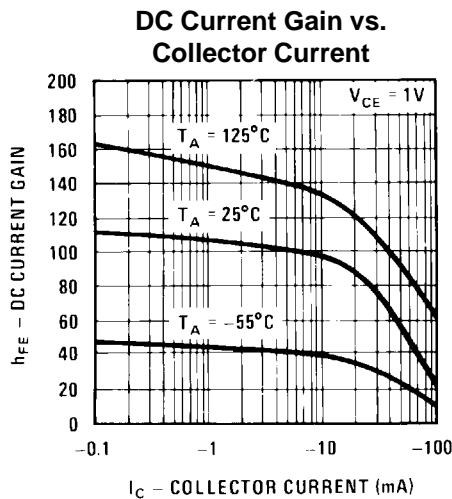
h_{FE}	DC Current Gain	$I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$	60		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 5.0 \text{ mA}, I_B = 0.5 \text{ mA}$		0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$		0.9	V

SMALL SIGNAL CHARACTERISTICS

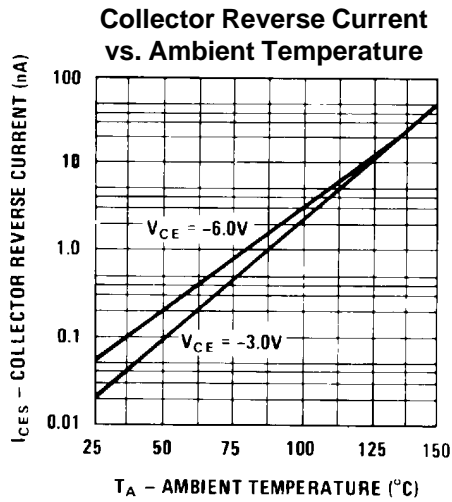
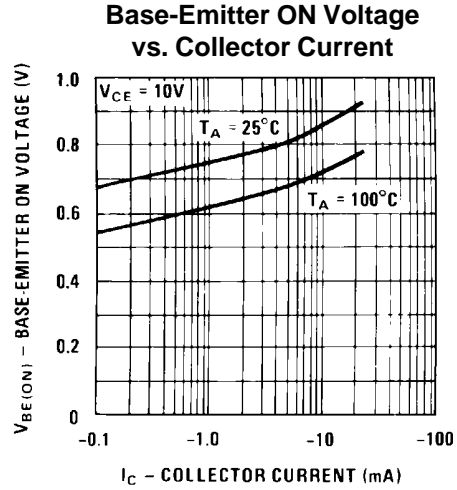
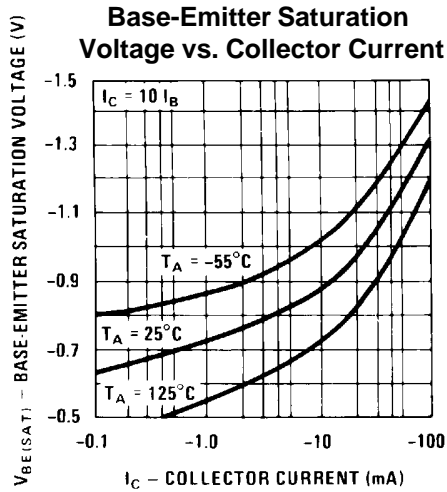
f_T	Current Gain - Bandwidth Product	$I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	600		MHz
C_{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		0.85	pF
C_{ce}	Collector Emitter Capacitance	$V_{CB} = 10 \text{ V}, I_B = 0, f = 1.0 \text{ MHz}$		0.65	pF

*Pulse Test: Pulse Width $\leq 300 \text{ } \mu\text{s}$, Duty Cycle $\leq 2.0\%$

DC Typical Characteristics

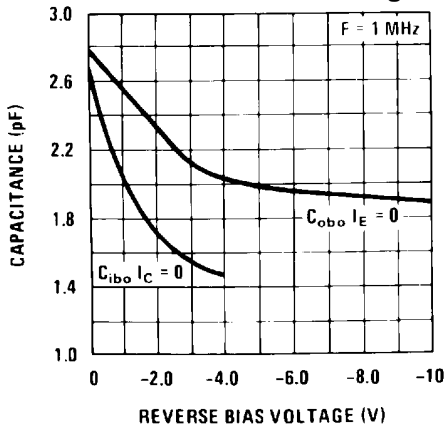


DC Typical Characteristics (continued)

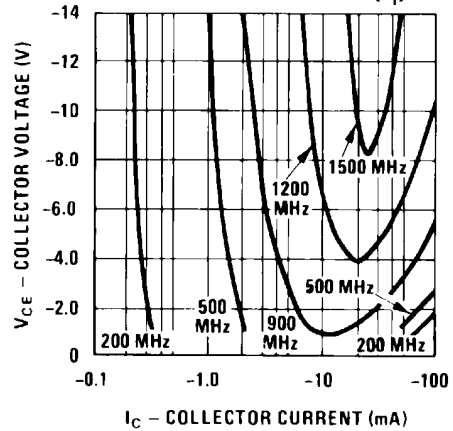


AC Typical Characteristics

Input / Output Capacitance vs. Reverse Bias Voltage



Contours of Constant Gain Bandwidth Product (f_T)



POWER DISSIPATION vs AMBIENT TEMPERATURE

